

## ABSTRACT

The present invention relates to a novel solution for the removal of post-etch residues having improved properties and to the use thereof in the production of semiconductors. The invention relates, in particular, to an aqueous solution  
5 having a reduced etching rate on metallisations and on surfaces which have to be freed from post-etch residues and particles during the semiconductor production process.

10

15

20

25

30

35